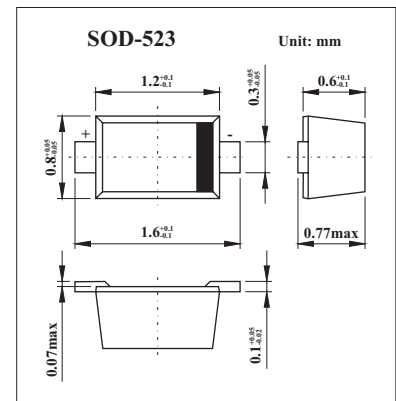


1PS79SB70

■ Features

- Low forward voltage
- High breakdown voltage
- Guard ring protected
- Ultra small plastic SMD package.
- Low capacitance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V _R			70	V
continuous forward current	I _F			70	mA
repetitive peak forward current	I _{FSM}	t _p ≤ 1 s; δ ≤ 0.5		70	mA
non-repetitive peak forward current	I _{FSM}	t _p < 10 ms		100	mA
storage temperature	T _{stg}		-65	+150	°C
junction temperature	T _j			150	°C
operating ambient temperature	T _{amb}		-65	+150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Max	Unit
continuous forward voltage	V _F	I _F = 1 mA	410	mV
		I _F = 10 mA	750	mV
		I _F = 15 mA	1	V
capacitance reverse current	I _R	V _R = 50 V, note 1	100	nA
		V _R = 70 V, note 1	10	μA
diodes capacitance	C _d	V _R = 0 V, f = 1 MHz	2	pF

Note

1. Pulse test: t_p = 300 μs, δ = 0.02.

■ Marking

Marking	G
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